Shottky barrier diode

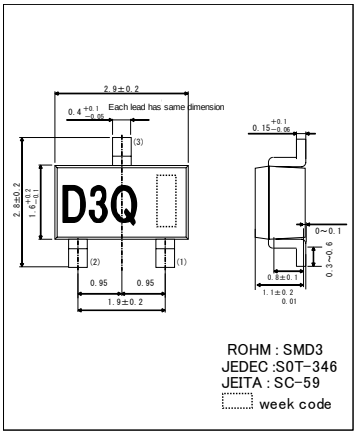
RB495D

●**Application**
General rectification.

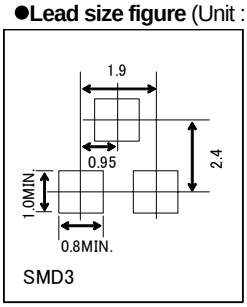
●**Features**
1) Small mold type. (SMD3)
2) Low I_R
3) High reliability.

●**Structure**
Silicon epitaxial planar

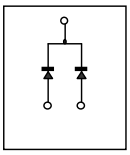
●**External dimensions** (Unit : mm)



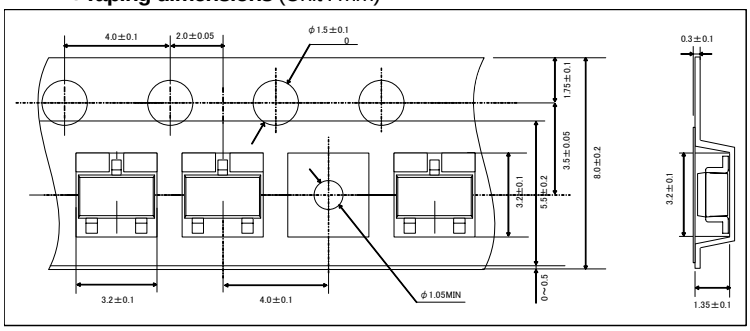
●**Lead size figure** (Unit : mm)



●**Structure**



●**Taping dimensions** (Unit : mm)



●**Absolute maximum ratings** (Ta=25°C)

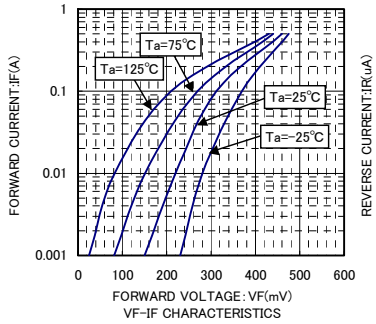
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	25	V
Average rectified forward current (*1)	Io	0.4	A
Forward current surge peak (60Hz・1cyc)	I_{FSM}	2	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-40 to +125	℃

(*1)Rating of per diode : Io/2

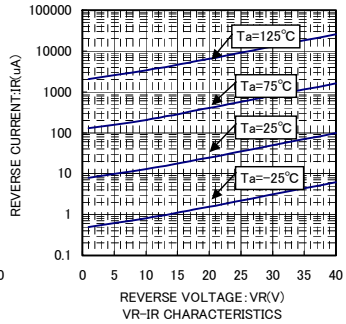
●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F1	-	-	0.30	V	I_F=10mA
	V_F2	-	-	0.50	V	I_F=200mA
Reverse current	I_R1	-	-	70	μA	V_R=25V

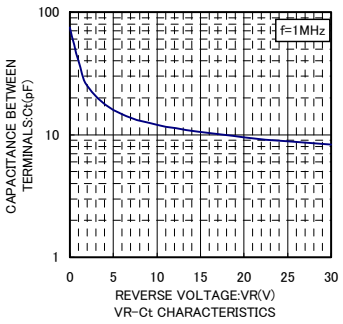
●**Electrical characteristic curves** (Ta=25°C)



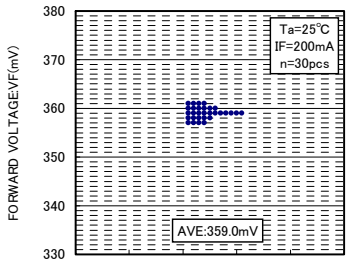
VF-IF CHARACTERISTICS



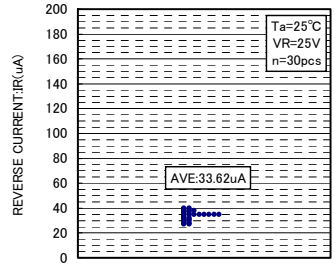
VR-IR CHARACTERISTICS



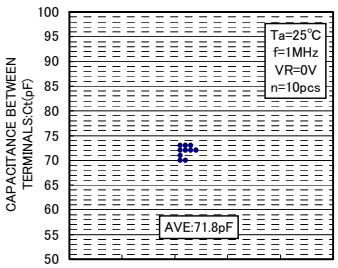
VR-Ct CHARACTERISTICS



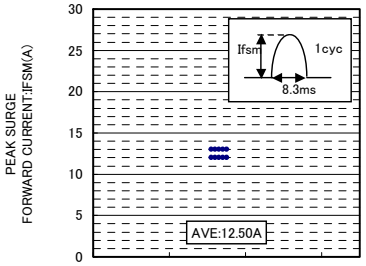
VF DISPERSION MAP



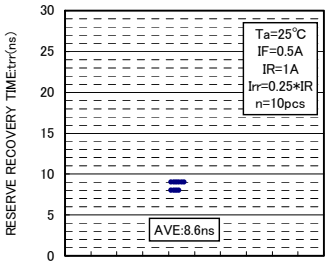
IR DISPERSION MAP



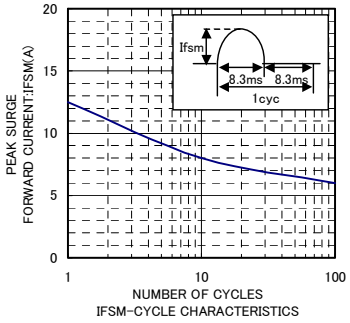
Ct DISPERSION MAP



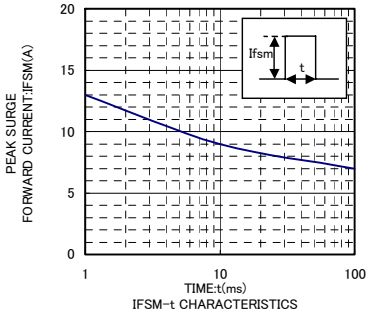
IFSM DISRESION MAP



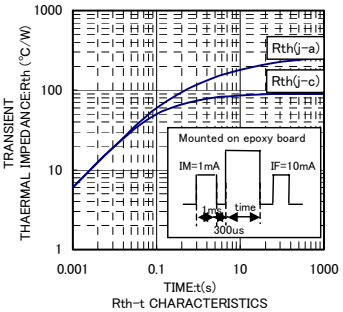
trr DISPERSION MAP



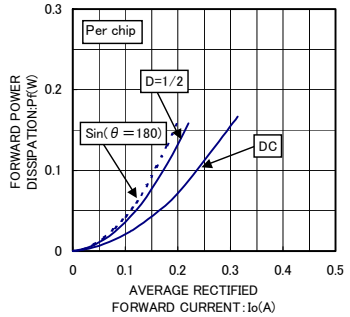
IFSM-CYCLE CHARACTERISTICS



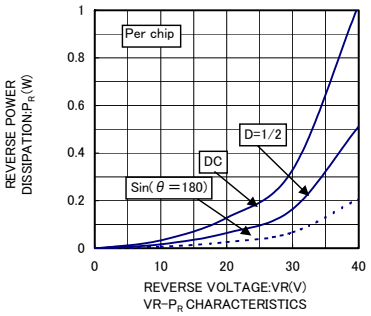
IFSM-t CHARACTERISTICS

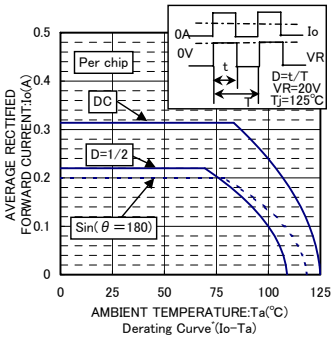


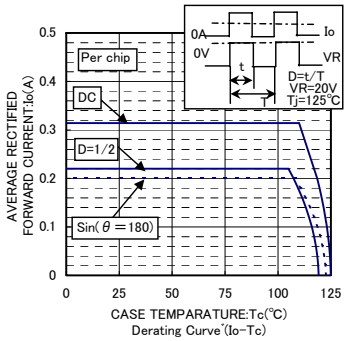
Rth-t CHARACTERISTICS



Io-Pf CHARACTERISTICS







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